AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1 – 12. (Canceled)

13. (Currently Amended) A method of fabricating a semiconductor device including a ~~hole~~ pattern, comprising the steps of:

employing linearly polarized light to transfer on a resist film formed on a wafer a mask pattern formed on a mask;

patterning said resist film; and

employing said resist film patterned to form [[a]] said pattern, wherein

to form said ~~hole~~ pattern said mask pattern has an opening larger in width in a first direction parallel to said linearly polarized light's direction of polarization than a second direction orthogonal to said first direction, and

said pattern is substantially the same width in said first and said second directions ~~wherein said mask pattern has a halftone region.~~

14 – 17. (Canceled)

18. (New) The method of fabricating a semiconductor device according to claim 13, wherein said pattern is a substantially round hole pattern.

19. (New) The method of fabricating a semiconductor device according to claim 13, wherein said opening of said mask pattern is obtained by dimensional correction of a substantially square geometry as a designed pattern.

20. (New) The method of fabricating a semiconductor device according to claim 13, wherein said mask pattern has a halftone region.

21. (New) The method of fabricating a semiconductor device according to claim 13, wherein said first direction is the direction in which said linearly polarized light used for exposure provides S polarized illumination, and said second direction is the direction in which said linearly polarized light used for exposure provides P polarized illumination.

22. (New) The method of fabricating a semiconductor device according to claim 13, wherein said opening has a ratio between said first direction and said second direction within a range of approximately 1.2 to 2.

23. (New) The method of fabricating a semiconductor device according to claim 13, wherein said opening has a ratio between said first direction and said second direction of approximately 1.6.

24. (New) The method of fabricating a semiconductor device according to claim 20, wherein a transmittance of said halftone region is within a range of approximately 2% to 25%.

25. (New) The method of fabricating a semiconductor device according to claim 20, wherein a transmittance of said halftone region is approximately 6%.